

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|------|--|-------|------------------|---------|------------------|
| L1 | 336 | MOS and transistor and conductivity and n-type and p-type and region and mask and trench and metal and plug and contact | USPAT | OR | ON | 2005/04/02 15:08 |
| L2 | 25 | MOS and transistor and conductivity and n-type and p-type and region and mask and trench and metal and plug and contact and crystallographic and orientation | USPAT | OR | ON | 2005/04/02 15:09 |
| L3 | 0 | MOS and transistor and conductivity and n-type and p-type and region and mask and trench and metal and plug and contact and crystallographic and orientation and dpoed and polysilicon and isolation and conductive and gate | USPAT | OR | ON | 2005/04/02 15:10 |
| L4 | 21 | MOS and transistor and conductivity and n-type and p-type and region and mask and trench and metal and plug and contact and crystallographic and orientation and doped and polysilicon and isolation and conductive and gate | USPAT | OR | ON | 2005/04/02 15:20 |
| L5 | 1 | MOS and transistor and conductivity and n-type and p-type and region and mask and trench and metal and plug and contact and crystallographic and orientation and doped and polysilicon and isolation and conductive and gate and NMOS | USPAT | OR | ON | 2005/04/02 15:12 |
| L6 | 0 | MOS and transistor and conductivity and n-type and p-type and region and mask and trench and metal and plug and contact and crystallographic and orientation and (first adj region) and (second adj region) and (third adj region) and (fourth adj region) | USPAT | OR | ON | 2005/04/02 15:13 |
| L7 | 1 | MOS and transistor and conductivity and n-type and p-type and region and mask and trench and metal and plug and contact and crystallographic and orientation and first and second and third and fourth | USPAT | OR | ON | 2005/04/02 15:17 |

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|-----|------|--|-----------------|----|-----|------------------|
| L8 | 1 | "6075276".PN. | USPAT; USOCR | OR | ON | 2005/04/02 15:14 |
| L9 | 1 | "4484206".PN. | USPAT; USOCR | OR | ON | 2005/04/02 15:14 |
| L10 | 1 | "4419681".PN. | USPAT; USOCR | OR | ON | 2005/04/02 15:15 |
| L11 | 1 | ("6639031").PN. | USPAT | OR | OFF | 2005/04/02 15:17 |
| L12 | 432 | MOS and transistor and (first adj region) and (second adj region) and (third adj region) and (fourth adj region) | USPAT | OR | ON | 2005/04/02 15:21 |
| L13 | 8 | MOS and transistor and (first adj region) and (second adj region) and (third adj region) and (fourth adj region) and conductivity and crystallographic and orientation | USPAT | OR | ON | 2005/04/02 15:29 |
| L14 | 628 | 257/69 | USPAT | OR | ON | 2005/04/02 15:29 |
| L15 | 1175 | 257/192 | USPAT | OR | ON | 2005/04/02 15:30 |
| L16 | 787 | 257/197 | USPAT | OR | ON | 2005/04/02 15:30 |
| L17 | 339 | 257/213 | USPAT | OR | ON | 2005/04/02 15:30 |
| L18 | 950 | 257/288 | USPAT | OR | ON | 2005/04/02 15:30 |
| L19 | 882 | 257/324 | USPAT | OR | ON | 2005/04/02 15:30 |
| L20 | 3165 | 257/347 | USPAT | OR | ON | 2005/04/02 15:30 |